

POSTAL Book Package

2023

ESE Electronics Engineering Conventional Practice Sets

Analog Circuits

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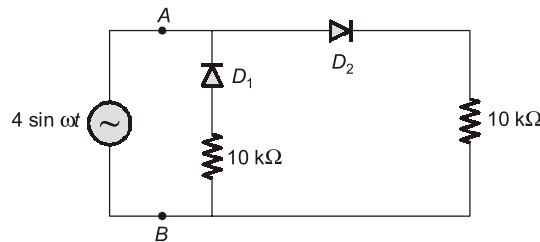


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Diode Circuits

Q1 A voltage source $V_{AB} = 4 \sin \omega t$, is applied across the terminals A and B of the circuit. The diodes are assumed to be ideal. Find the impedance offered by the circuit across the terminals A and B in kilo ohm.



Solution:

In +ve half cycle D_1 – off (R.B.)

D_2 – on (F.B.)

∴ Equivalent circuit will be

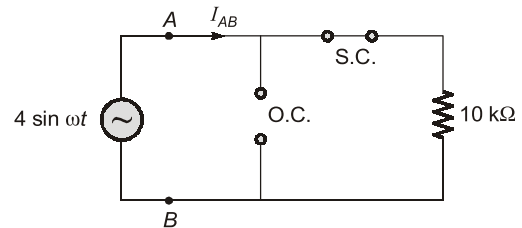
∴

$$V_{AB} = 4 \sin \omega t$$

$$I_{AB} = \frac{V_{AB}}{10 \text{ k}\Omega}$$

∴

$$R_i = \frac{V_{AB}}{I_{AB}} = 10 \text{ k}\Omega$$



For –ve half cycle,

D_1 on, D_2 off

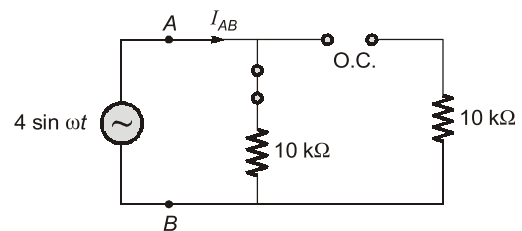
Equivalent circuit,

$$V_{AB} = 4 \sin \omega t$$

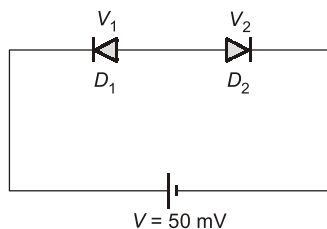
$$I_{AB} = \frac{4 \sin \omega t}{10 \text{ k}\Omega}$$

∴

$$\frac{V_{AB}}{I_{AB}} = R_i = 10 \text{ k}\Omega$$



Q2 Two ideal and identical junction diodes are connected as shown in Figure. If the current through the reverse-biased diode is I_0 and is constant, explain the circuit operation when both the diodes are connected in forward-biased condition. Assume $V_T = 25 \text{ mV}$, $V_\gamma = 0.7 \text{ V}$ and $\eta = 1$ for the diodes.



Solution:

Case 1: Diode D_1 is in reverse bias where as D_2 is forward biased.

At Node 'a'

$$I_1 + I_2 = 0$$

$$I_1 = -I_2$$

$$I_S \left(e^{-\frac{V_1}{\eta V_T}} - 1 \right) = -I_S \left(e^{\frac{+V_2}{\eta V_T}} - 1 \right)$$

$$e^{-\frac{V_1}{\eta V_T}} + e^{\frac{V_2}{\eta V_T}} = 2$$

Also,

$$V_2 = 50 - V_1$$

$$\therefore e^{-\frac{V_1}{\eta V_T}} + e^{\frac{50 - V_1}{\eta V_T}} = 2$$

$$e^{-\frac{V_1}{\eta V_T}} \left[1 + e^{\frac{50}{\eta V_T}} \right] = 2$$

$$e^{-\frac{V_1}{V_T}} = \frac{2}{1 + e^2}$$

$$e^{-\frac{V_1}{V_T}} = \frac{2}{3.39} = 0.24$$

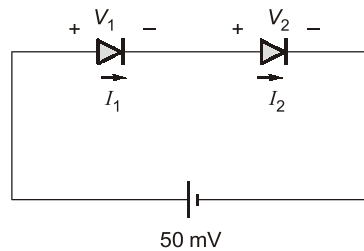
Putting in I_1 ,

$$I_1 = I_0 = I_S \left[e^{-\frac{V_1}{V_T}} - 1 \right]$$

$$I_1 = I_0 = -0.76 I_S$$

-ve sign denotes that direction of current will be opposite to the assumed direction.

Case 2: Both the diodes are forward biased.



As both diodes are ideal and identical hence voltage drop across both diodes will be same.

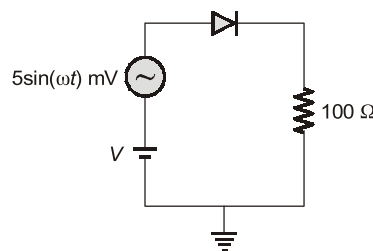
$$\therefore V_1 = V_2 = 25 \text{ mV}$$

$$\text{Now, } I_1 = I_2 = I_S \left(e^{\frac{V_1}{V_T}} - 1 \right) = I_S \left(e^{\frac{25}{25}} - 1 \right) = 1.72 I_S$$

$$\frac{I_1}{I_0} = \frac{1.72 I_S}{0.76 I_S} = 2.26$$

$$\therefore I_1 = 2.26 I_0$$

Q3 A DC current of $26 \mu\text{A}$ flows through the circuit shown. The diode in the circuit is forward biased and it has an ideality factor of one. At the quiescent point, the diode has a junction capacitance of 0.5 nF . Its neutral region resistances can be neglected. Assume that the room temperature thermal equivalent voltage is 26 mV .



For $\omega = 2 \times 10^6 \text{ rad/s}$, the amplitude of the small-signal component of diode current.

Solution:

The small-signal equivalent model of the given circuit can be drawn as shown below.

Given that,

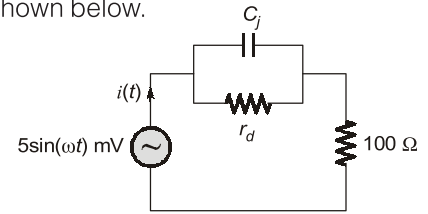
$$\omega = 2 \times 10^6 \text{ rad/sec}$$

$$C_j = 0.5 \text{ nF}$$

$$I_{DC} = 26 \mu\text{A}$$

$$V_T = 26 \text{ mV}$$

$$\eta = 1$$



Since, small signal incremental diode resistance, $r_d = \frac{\eta V_T}{I_{DC}} = \frac{26 \text{ mV}}{26 \mu\text{A}} = 1 \text{ k}\Omega$

and impedance due to junction capacitance, $\frac{1}{\omega C_j} = \frac{1}{2 \times 10^6 \times 0.5 \times 10^{-9}} \Omega = 1 \text{ k}\Omega$

So, total impedance of the circuit will be,

$$Z = \left(r_d \parallel \frac{1}{j\omega C_j} \right) + 100 \Omega$$

$$\left(r_d \parallel \frac{1}{j\omega C_j} \right) = \frac{(1000)(-j1000)}{1000 - j1000} \Omega = \frac{-j(1+j)}{2} \text{ k}\Omega = \frac{1}{2}(1-j) \text{ k}\Omega = (500 - j500) \Omega$$

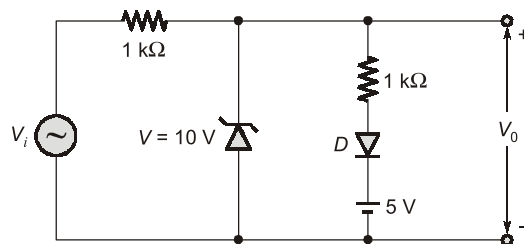
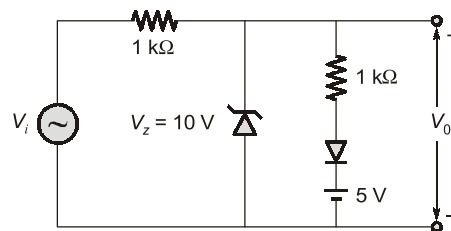
\therefore

$$Z = 600 - j500 \Omega$$

$$|Z| = 100\sqrt{36 + 25} = 100\sqrt{61} \Omega$$

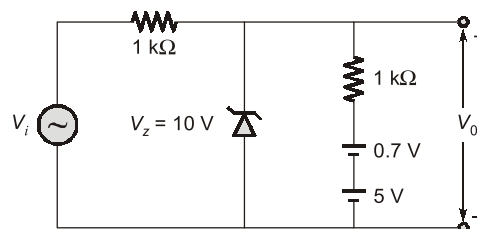
$$I_m = \frac{V_m}{|Z|} = \frac{5 \text{ mV}}{100\sqrt{61} \Omega} = \frac{50}{\sqrt{61}} \mu\text{A} = 6.40 \mu\text{A}$$

Q4 Assuming forward voltage drop across diodes to be 0.7 V, draw the transfer characteristic of the clipper circuit shown in figure.

**Solution:**

When V_i is +ve and $V_i > 5.7 \text{ V}$

Assume diode is conducting,



Assume the Zener diode is reverse biased and having voltage less than breakdown voltage

$$V_i - I(1 \text{ k}\Omega) - I(1 \text{ k}\Omega) - 0.7 - 5 = 0$$

$$V_i - I(2 \text{ k}\Omega) - 5.7 = 0$$

$$I(2 \text{ k}\Omega) = V_i - 5.7$$

$$I = \left(\frac{V_i - 5.7}{2 \text{ k}\Omega} \right)$$

$$V_0 = 5.7 + 1 \times I$$

$$= 5.7 + \left(\frac{V_i - 5.7}{2} \right) = \left(\frac{5.7 + V_i}{2} \right)$$

When,

$$V_i < 5.7 \text{ V}$$

$$V_0 = V_i$$

If,

$$5.7 < V_i < 14.3$$

(\because Diode is in off state)

$$V_0 = \left(\frac{5.7 + V_i}{2} \right)$$

Diode conducts and Zener diode is reverse biased,

When,

$$V_i > 14.3 \text{ V}$$

\Rightarrow

$$V_0 = 10 \text{ volts}$$

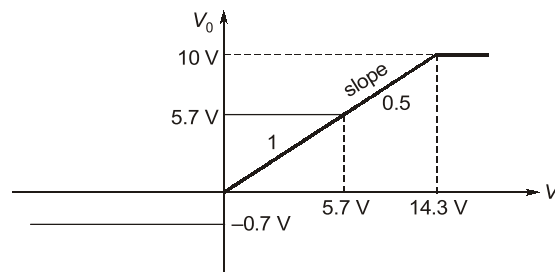
Breakdown occurs in Zener diode.

When,

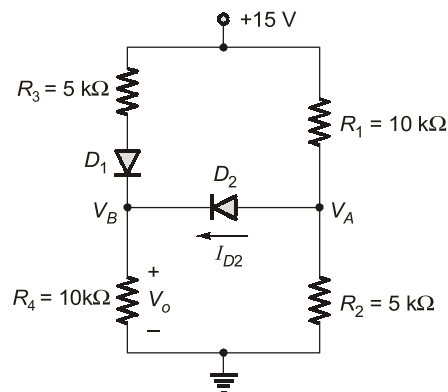
$$V_i < 0 \text{ V}$$

$$V_0 = -0.7 \text{ V}$$

Transfer characteristics:



Q5 Determine the current I_{D2} and the voltage V_0 in the multidiode circuit shown in the figure below. Assume that, cut-in voltage $V_\gamma = 0.7 \text{ V}$ for each diode.



Solution:

To begin, initially assume that, both the diodes D_1 and D_2 are in their conducting state.

By applying KCL at A and B nodes, we have

$$\frac{15 - V_A}{10} = I_{D2} + \frac{V_A}{5}$$

...(i)

$$\text{and } \frac{15 - (V_B + 0.7)}{5} + I_{D2} = \frac{V_B}{10} \quad \dots(\text{ii})$$

We note that $V_B = V_A - 0.7$. Combining the two equations and eliminating I_{D2} , we find

$$V_A = 7.62 \text{ V} \quad \text{and} \quad V_B = 6.92 \text{ V}$$

From equation (i) above, we obtain

$$\frac{15 - 7.62}{10} = I_{D2} + \frac{7.62}{5} \Rightarrow I_{D2} = -0.786 \text{ mA}$$

We assumed that D_2 was ON, so a negative current is inconsistent with that initial assumption.

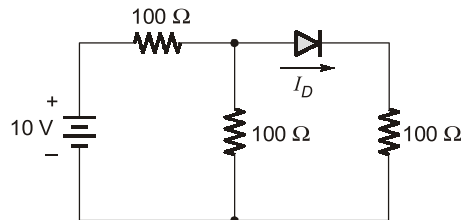
Now assume that diode D_2 is OFF and D_1 is ON. To find the node voltages, we can simply use voltage divider principle as

$$V_A = \left(\frac{5}{5 + 10} \right) (15) = 5 \text{ V}$$

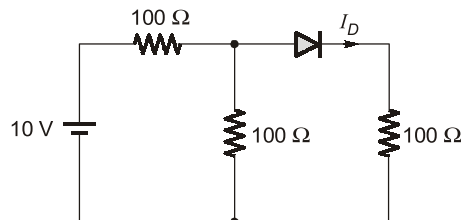
$$\text{and } V_B = V_o = \left(\frac{10}{10 + 5} \right) (15 - 0.7) = 9.53 \text{ V}$$

These voltages show that diode D_2 is indeed reverse biased so that $I_{D2} = 0$.

Q6 Find the diode current I_D in the circuit shown below when the diode has cut in voltage, $V_y = 0.7 \text{ V}$ and forward resistance, $R_f = 25 \Omega$.

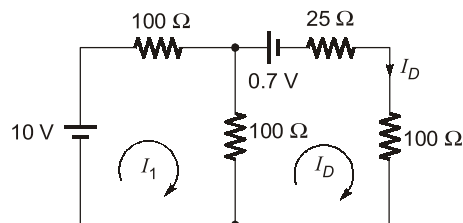
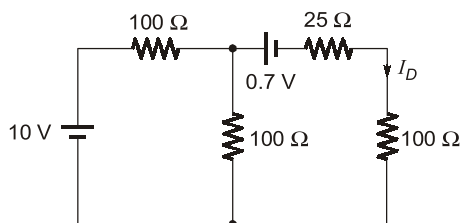


Solution:



Given : Diode cut-in voltage = 0.7 V and diode forward resistance = 25 Ω

Replacing the diode with its equivalent, we get,



$$\text{Using KVL, } 10 - 100I_1 - 100(I_1 - I_D) = 0 \quad \dots(\text{i})$$

$$-0.7 - 25I_D + 100(I_1 - I_D) = 0 \quad \dots(\text{ii})$$

Solving equation (i) and (ii)

$$10 - 200I_1 - 100I_D = 0 \quad \dots(\text{iii})$$

$$-0.7 - 225I_D + 100I_1 = 0 \quad \dots(\text{iv})$$

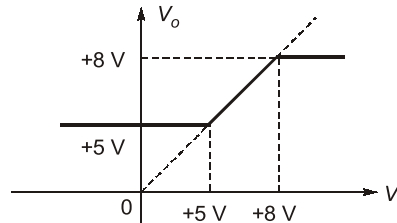
Multiplying equation (iv) by 2 and adding, we get

$$10 - 1.4 - 450I_D - 100I_D = 0$$

$$8.6 = 550I_D$$

$$\therefore I_D = \frac{8.6}{550} = 15.63 \text{ mA}$$

Q7 The ideal transfer characteristic of a particular circuit is given in figure. Design the circuit. Draw the output waveform with proper explanation, if $V_i = 10 \sin \omega t$.



Solution:

Slope of the curve between A and B is

$$m = \frac{(8-5)}{(8-5)} = 1$$

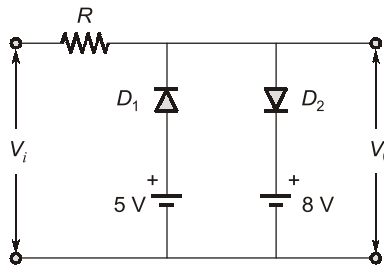
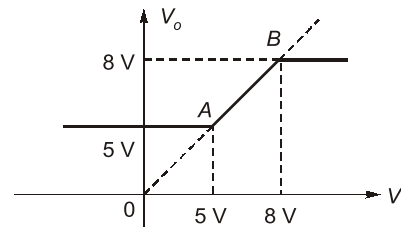
The circuit diagram for the above input-output (transfer) characteristic is a two-level clipper as shown below.

Cut in voltages of diodes are zero.

For $V_i < 5 \text{ V} \rightarrow$ diode D_1 will be on and D_2 will be off

and

$$V_o = 5 \text{ V}$$



For $V_i > 8 \text{ V} \rightarrow$ diode D_1 will be off and diode D_2 will be on

and

$$V_o = 8 \text{ V}$$

For $5 < V_i < 8 \text{ V} \rightarrow$ both the diodes will be off

and

$$V_o = V_i$$

Given that

$$V_i = 10 \sin \omega t$$

or

$$V_i = 10 \sin \theta$$

$$(\omega t = \theta)$$

For $V_i < 5$;

$$10 \sin \theta < 5 \Rightarrow 0 < \theta < 30^\circ \text{ and } 150^\circ < \theta < 360^\circ$$

$$V_o = 5 \text{ V}$$

For $V_i > 8 \text{ V}$;

$$10 \sin \theta > 8 \Rightarrow 53.13^\circ < \theta < 126.869^\circ$$

$$V_o = 8 \text{ V}$$

For $5 < V_i < 8 \text{ V}$;

$$30^\circ < \theta < 53.13^\circ \text{ and } 126.87^\circ < \theta < 150^\circ$$

$$V_o = V_i$$

The required voltage-current characteristics can be written as

$$V_o = \begin{cases} 5 \text{ V} & ; V_i < 5 \text{ V} \\ V_i & ; 5 \text{ V} < V_i < 8 \text{ V} \\ 8 \text{ V} & ; V_i > 8 \text{ V} \end{cases}$$